Abstract:

Method for Producing a Polished Semiconductor

The invention relates to a method for producing a semiconductor wafer, the semiconductor wafer being cut from a crystal and subjected to a series of processing steps in which material is removed from a front side and a rear side of the semiconductor wafer, comprising the following processing steps:
a mechanical processing step,
an etching step in which the semiconductor wafer is oxidized and material is removed from the front side of the semiconductor wafer with the aid of a gaseous etchant which contains hydrofluoric acid at a temperature of from 20 to 70°C,
and a polishing step in which the front side of the semiconductor wafer is polished, the processing steps in which the front side of the semiconductor wafer is polished causing material removal which does not amount to more than 5 µm in total.